

# IRF7831UTRPBF-VB Datasheet

## N-Channel 30-V (D-S) MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
30	0.003 at $V_{GS} = 10$ V	25
	0.004 at $V_{GS} = 4.5$ V	22

### FEATURES

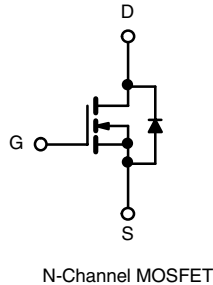
- Halogen-free According to IEC 61249-2-21 Available
- Ultra Low On-Resistance Using High Density Trench Power MOSFET Technology



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### APPLICATIONS

- Synchronous Buck Low-Side
  - Notebook
  - Server
  - Workstation
- Synchronous Rectifier-POL



### ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$ , unless otherwise noted

Parameter	Symbol	10 s	Steady State	Unit
Drain-Source Voltage	$V_{DS}$	30		V
Gate-Source Voltage	$V_{GS}$	$\pm 20$		
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ ) <sup>a</sup>	$I_D$	25	17	A
		20	13	
Pulsed Drain Current (10 $\mu\text{s}$ Pulse Width)	$I_{DM}$	70		
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	2.9	1.3	
Avalanche Current	$I_{AS}$	50		
Maximum Power Dissipation <sup>a</sup>	$P_D$	3.5	1.6	W
		2.2	1	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150		$^\circ\text{C}$

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	29	35	$^\circ\text{C/W}$
		67	80	
Maximum Junction-to-Foot (Drain)	$R_{thJF}$	13	16	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	1.0		3.0	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30\text{ V}$ , $V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 30\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 55\text{ }^{\circ}\text{C}$			5	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$ , $V_{GS} = 10\text{ V}$	30			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 25\text{ A}$		0.003		$\Omega$
		$V_{GS} = 4.5\text{ V}$ , $I_D = 22\text{ A}$		0.004		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}$ , $I_D = 25\text{ A}$		110		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 2.9\text{ A}$ , $V_{GS} = 0\text{ V}$		0.72	1.1	V
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15\text{ V}$ , $V_{GS} = 4.5\text{ V}$ , $I_D = 20\text{ A}$		6500		pF
Output Capacitance	$C_{oss}$			930		
Reverse Transfer Capacitance	$C_{rss}$			610		
Total Gate Charge	$Q_g$	$V_{DS} = 15\text{ V}$ , $V_{GS} = 4.5\text{ V}$ , $I_D = 20\text{ A}$		45	70	nC
Gate-Source Charge	$Q_{gs}$			20		
Gate-Drain Charge	$Q_{gd}$			16		
Gate Resistance	$R_g$	$f = 1.0\text{ MHz}$		1.1		$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}$ , $R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 6\text{ }\Omega$		27	40	ns
Rise Time	$t_r$			21	35	
Turn-Off Delay Time	$t_{d(off)}$			107	160	
Fall Time	$t_f$			43	65	
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = 2.9\text{ A}$ , $dI/dt = 100\text{ A}/\mu\text{s}$		45	70	

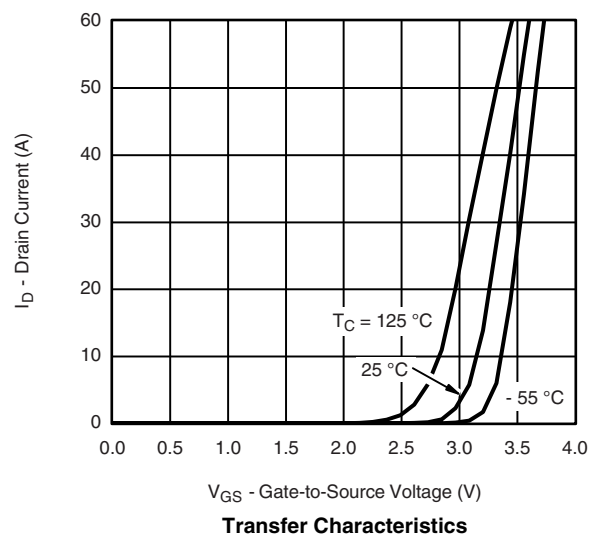
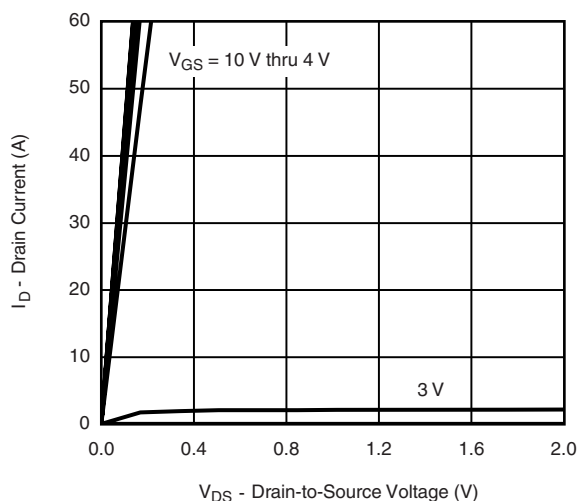
Notes:

a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

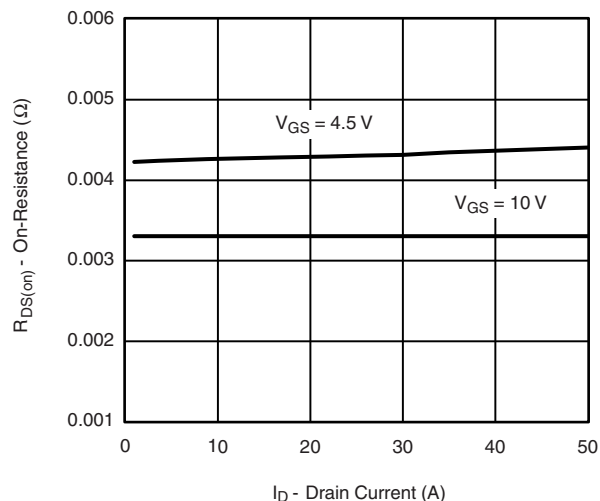
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

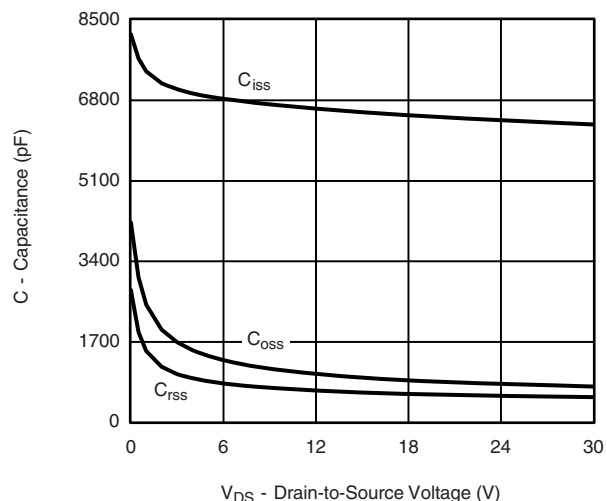
## TYPICAL CHARACTERISTICS $25\text{ }^{\circ}\text{C}$ , unless otherwise noted



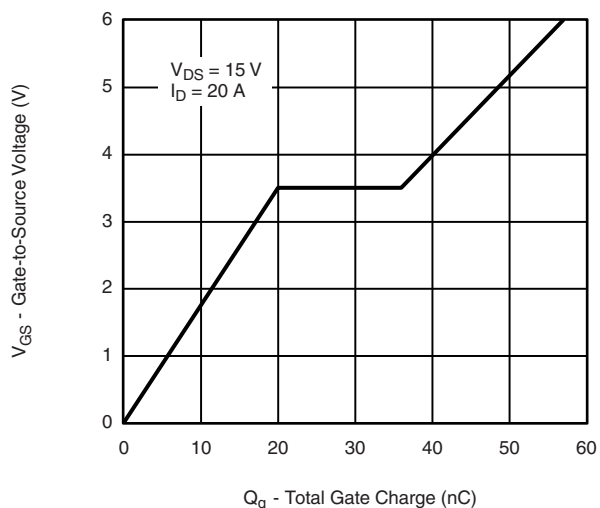
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**On-Resistance vs. Drain Current**



**Capacitance**



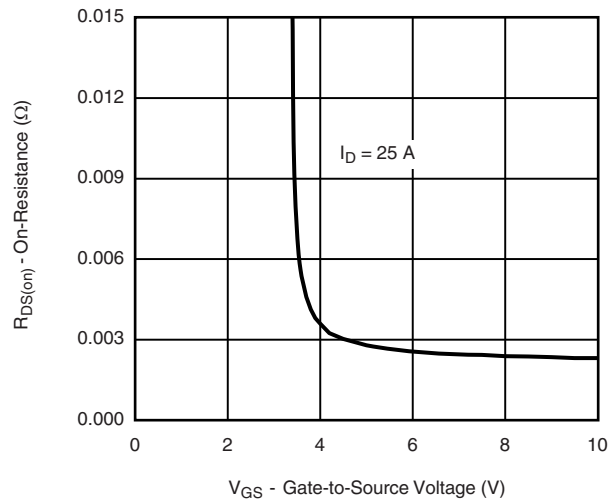
**Gate Charge**



**On-Resistance vs. Junction Temperature**

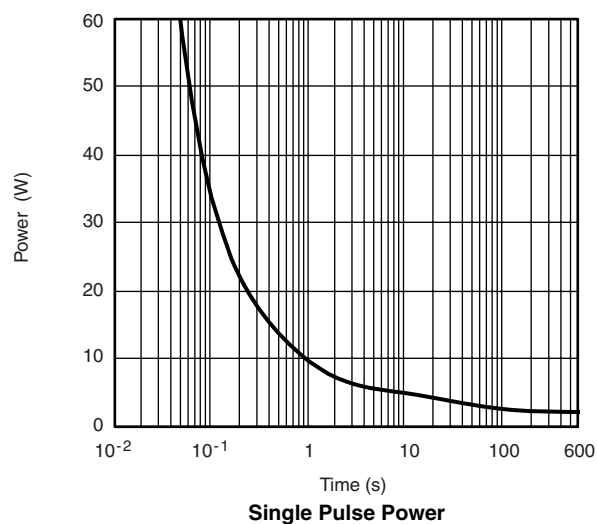
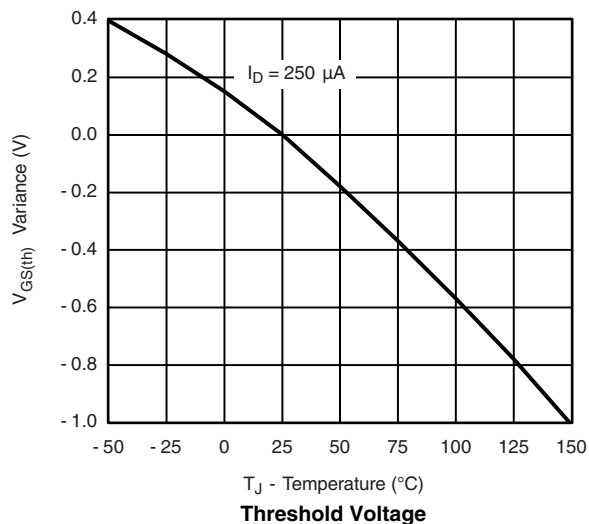


**Source-Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**

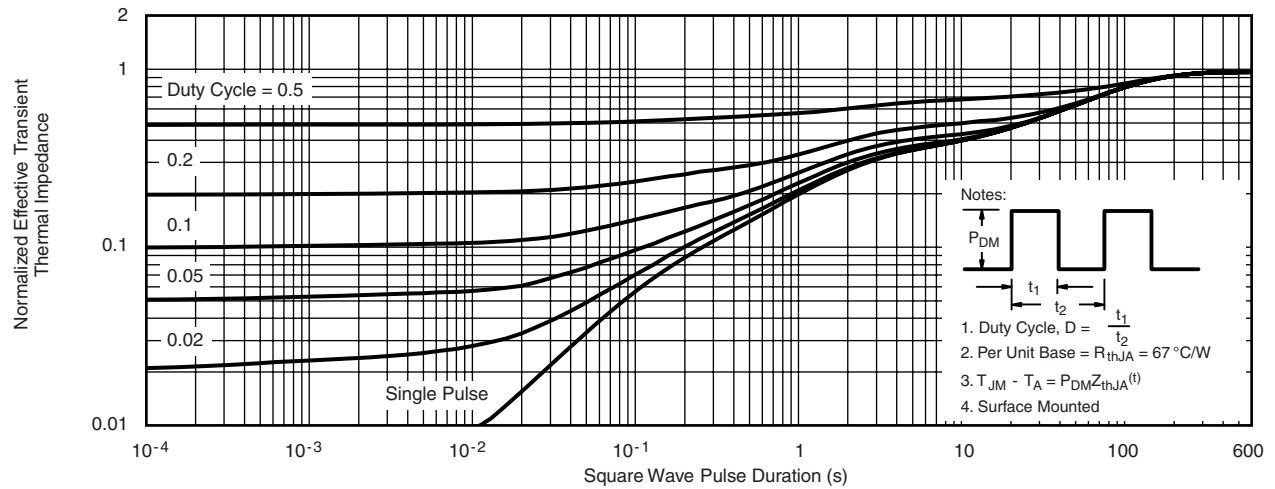
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



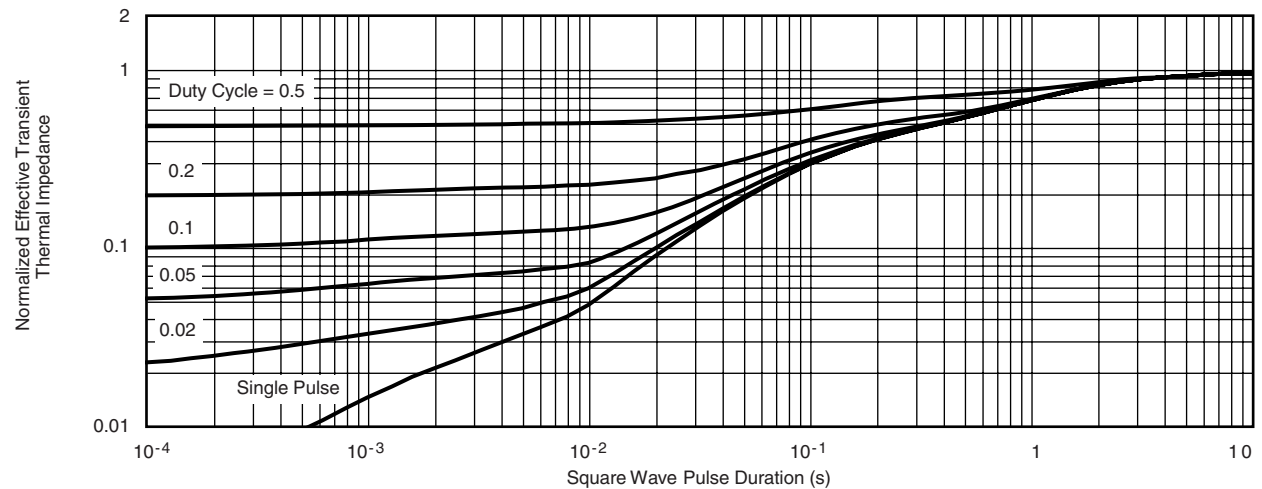
\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

**Safe Operating Area, Junction-to-Case**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



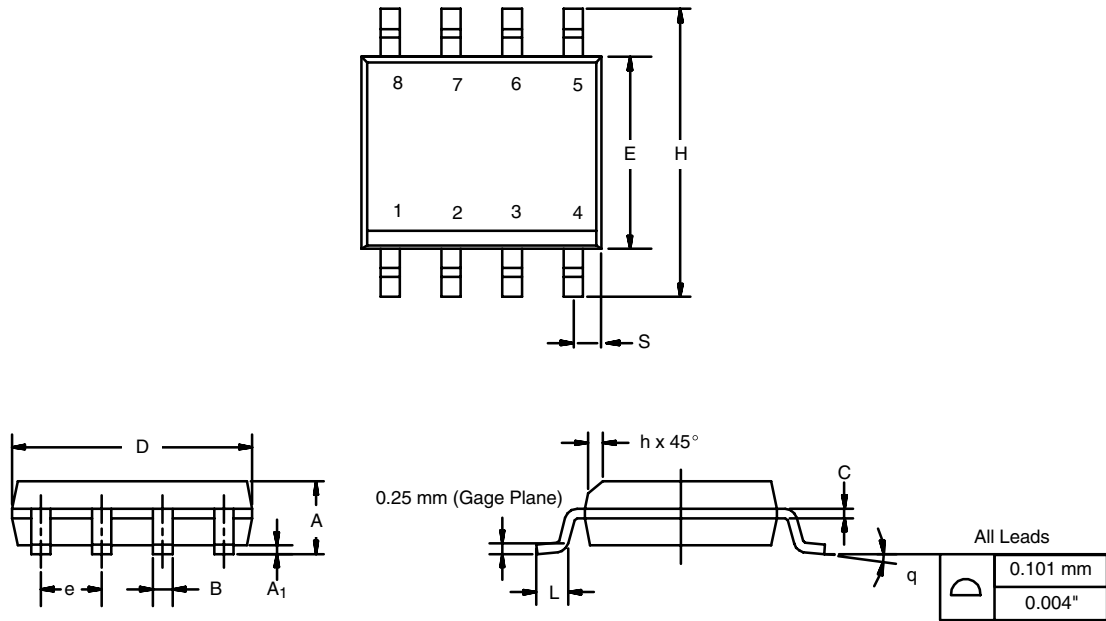
**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Foot**

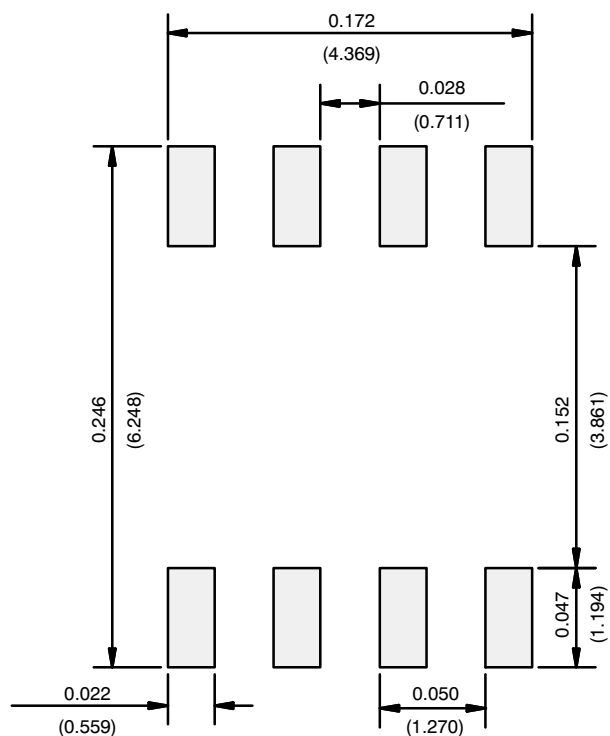
## SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

# RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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